

Marking Information

Site 1



8N = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	С		Н	I	J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



8N = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Year	2015	 2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	5	 0	1	2	3	4	5	6	7	8	9

Week	1-26	27-52	53
Code	A-Z	a-z	z

Γ	Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Γ	Code	Т	U	V	W	X	Υ	Z



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Characteristic				
Drain-Source Voltage	V_{DSS}	12	V		
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current, $V_{GS} = 4.5V$ (Note 6) Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			I _D	12.2 9.8	А
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%	6)		I _{DM}	60	Α
Continuous Source-Drain Diode Current (Note 6) T _A = +25°C			Is	1.8	Α
Avalanche Current, L = 0.1mH (Note 7)			I _{AS}	16.4	Α
Avalanche Energy, L = 0.1mH (Note 7)			E _{AS}	13.5	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	Б	0.7	W
Total Fower Dissipation (Note 5)	$T_A = +70^{\circ}C$	P_{D}	0.4	VV
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	168	°C/W
Total Dawar Dissination (Note 6)	T _A = +25°C	<u> </u>	1.7	W
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	P_{D}	1.0	VV
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	74	°C/W
Thermal Resistance, Junction to Case (Note 6)	·	R _{0JC}	12	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

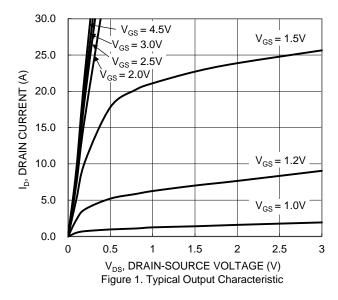
Electrical Characteristics ($@T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	12	1	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	-	1	μΑ	$V_{DS} = 9.6V, V_{GS} = 0V$
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	0.3	l	1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
			6.6	8		$V_{GS} = 4.5V, I_D = 5A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	7.6	11	mΩ	$V_{GS} = 3.0V, I_D = 5A$
			8.5	12.5		$V_{GS} = 2.5V, I_D = 5A$
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V$, $I_S = 5A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}		995	_		\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
Output Capacitance	C _{oss}		305	_	pF	$V_{DS} = 6V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}		270	_		1 = 1.000112
Gate Resistance	R_g		1.5	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	13.6	_		
Total Gate Charge (V _{GS} = 8V)	Qg	_	23.4	_	nC	V _{DS} = 6V. I _D = 5A
Gate-Source Charge	Q_{gs}	_	1.3	_	IIC	$V_{DS} = 6V, I_D = 5A$
Gate-Drain Charge	Q_{gd}		3.3	_		
Turn-On Delay Time	t _{D(ON)}	_	3.5	_		
Turn-On Rise Time	t _R	_	6.6	_	ns	$V_{DS} = 6V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t _{D(OFF)}	_	17.5	_	115	$R_G = 2\Omega$, $I_D = 5A$
Turn-Off Fall Time	t _F	_	7.5	_		
Reverse Recovery Time	t _{RR}	_	15	_	ns	I _F = 5A, di/dt = 200A/μs
Reverse Recovery Charge	Q _{RR}	_	4	_	nC	$I_F = 5A$, di/dt = 200A/ μ s

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







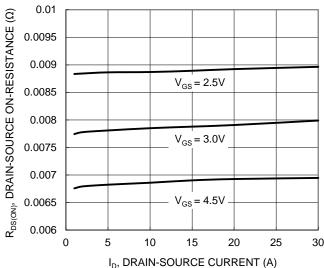


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

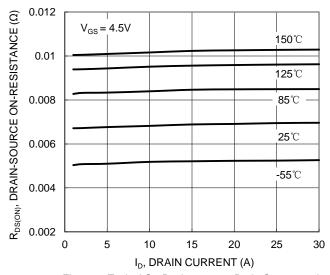


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

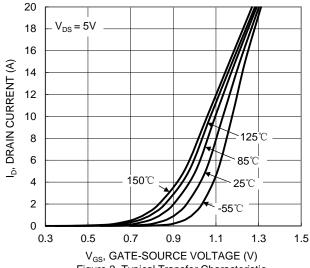


Figure 2. Typical Transfer Characteristic

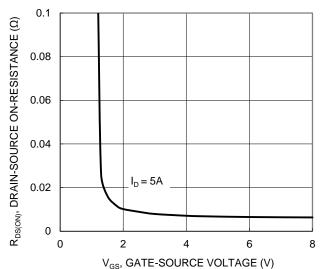


Figure 4. Typical Transfer Characteristic

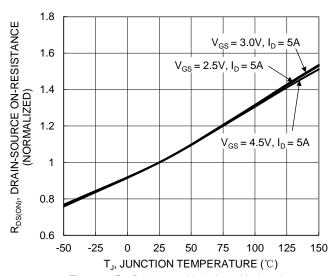


Figure 6. On-Resistance Variation with Junction Temperature





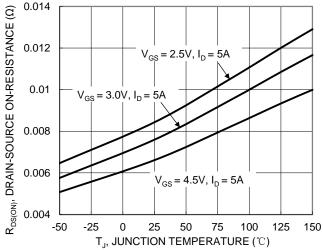


Figure 7. On-Resistance Variation with Junction Temperature

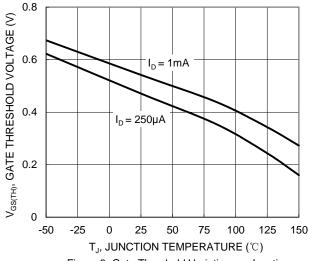
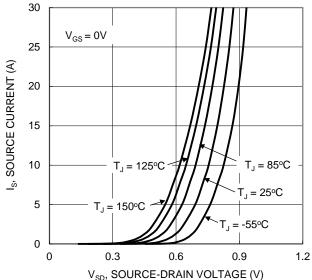
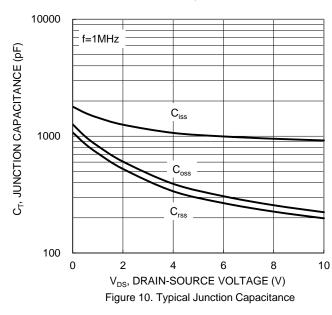


Figure 8. Gate Threshold Variation vs. Junction Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current



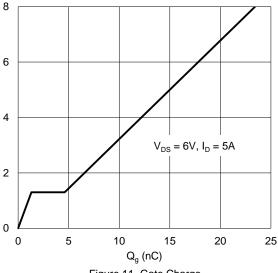
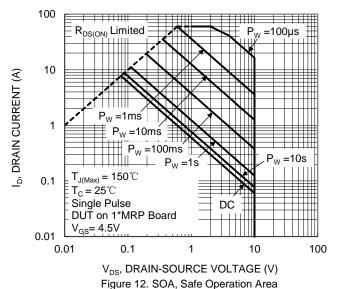


Figure 11. Gate Charge



 $V_{GS}(V)$



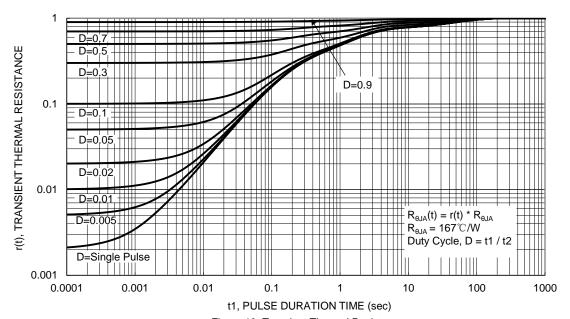


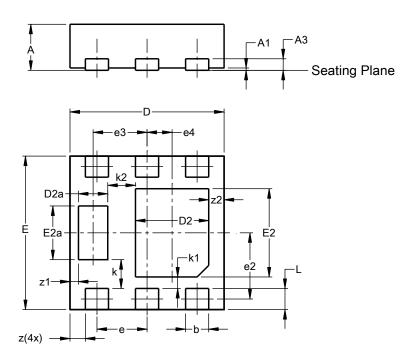
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

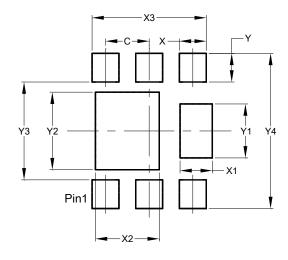


	U-DFN2020-6 (Type F)					
D:			-			
Dim	Min	Max	Тур			
Α	0.57	0.63	0.60			
A1	0.00					
A3	-	-	0.15			
b	0.25	0.35	0.30			
D	1.95	2.05	2.00			
D2	0.85	1.05	0.95			
D2a	0.33	0.33 0.43 0.				
Е	1.95	2.00				
E2	1.05	1.25	1.15			
E2a	0.65 0.75 0.7					
е		0.65 BS	С			
e2	C).863 BS	SC			
e3		0.70 BS	С			
e4	0).325 BS	SC			
k		0.37 BS	С			
k1	0.15 BSC					
k2	0.36 BSC					
L	0.225 0.325 0.275					
Z	0.20 BSC					
z 1	(0.110 BSC				
z2		0.20 BS				
All C	Dimens	ions in	mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
С	0.650
Х	0.400
X1	0.480
X2	0.950
Х3	1.700
Υ	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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